

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SD1220

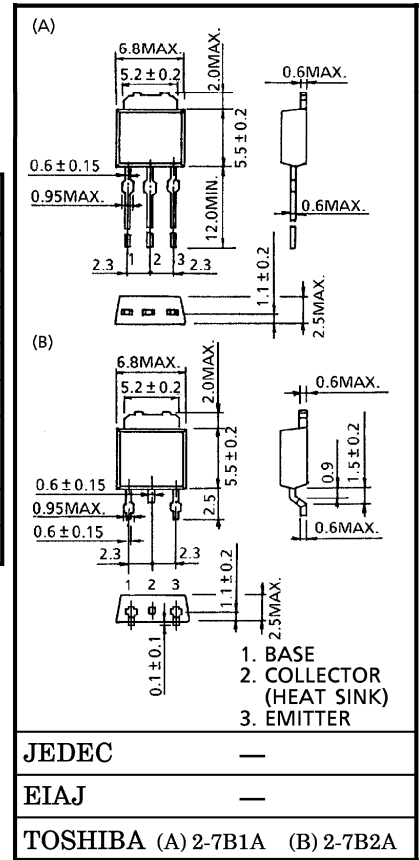
POWER AMPLIFIER APPLICATIONS

- Complementary to 2SB905

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	150	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	1.5	A
Base Current	I _B	1.0	A
Collector Power Dissipation	P _C	Ta = 25°C 1.0	W
		Tc = 25°C 10	
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

Unit in mm



Weight : 0.36 g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 150 V, I _E = 0	—	—	1.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 6 V, I _C = 0	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 10 mA, I _B = 0	150	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 200 mA	60	—	320	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 500 mA, I _B = 50 mA	—	—	1.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 5 V, I _C = 5 mA	0.5	—	0.8	V
Transition Frequency	f _T	V _{CE} = 5 V, I _C = 200 mA	20	100	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	—	13	20	pF

Note : h_{FE} Classification R : 60~120, O : 100~200, Y : 160~320

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